18ECO134T – Sensors and Transducers

Unit IV: Session 3: SLO 1

Hall effect

• Its also called as Galvanomagnetic effect sensor.

Observed in metals and semiconductors.

• When a current is sent through a very long strip of extrinsic homogenous semiconductor in the x direction and across the plane xy perpendicular to it, a magnetic field is applied to produce a flux density Bz, then an electric field Ey in the direction of y is produced which is called Hall field.

• With electrodes across the strip in y direction, a voltage VH called the Hall voltage, can be collected with approximately is given by

$$V_H \approx B_z I_x \tag{4.33}$$

• Galvanomagnetic effects, arise because of Lorentz force on the charge carrier transport phenomena in condensed medium. Lorentz force is

- µH Hall mobility
- Jo- current density due to electric field E
- Carrier concentration Δn
- A magnetic field also affect the electric field potential and carrier concentration and hence it is not justified to write J=J0 and B=0

$$\mathbf{J} = \mathbf{J}_0 + \mu_H [\mathbf{J}_0 \times \mathbf{B}] \tag{4.35}$$

- σ- conductivity
- D diffusion coefficient

$$\mathbf{J_0} = \sigma \mathbf{E} - e \mathbf{D} \nabla n \tag{4.36}$$

• Drift – Ist term, Diffusion –IInd term, transverse transport caused by magnetic field – IInd term of eq. 4.35

- The transport coefficients μH , σ , D are dependent on electric and magnetic field and are determined by carrier scattering process.
- Hall mobility μH is the product of drift mobility of the carrier μ and hall scattering factor r, which is given by appropriate ratio of relaxation time averages of their energy distribution, thus

$$r = \frac{\langle \tau^2 \rangle}{\langle \tau \rangle^2}$$

$$\mu_H = r\mu$$
(4.37a)
$$(4.37b)$$